Abstracts

GaAs Molecular Beam Epitaxy Monolithic Power Amplifiers at U-Band (1989 Vol. I [MWSYM])

G. Hegazi, H.-L.A. Hung, J.L. Singer, F.R. Phelleps, A.B. Cornfeld, T. Smith, J.F. Bass, H.E. Carlson and H.C. Huang. "GaAs Molecular Beam Epitaxy Monolithic Power Amplifiers at U-Band (1989 Vol. I [MWSYM])." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 209-213.

The design, fabrication, and measurements for 44-GHz band molecular beam epitaxy (MBE) monolithic power amplifiers are described. A five-stage balanced amplifier provided a linear gain of 15.1 dB and maximum output power of 500 mW at 42.5 GHz. These results may represent the highest power and gain achieved from a MIMIC in the 44-GHz band.

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